

3. (Once Amended) A method according to claim 1, wherein at least one precursor is supplied separately to the region as a gas stream.

4. (Once Amended) A method according to claim 1, wherein the species are chosen from the Group III and Group V elements.

5. (Once Amended) A method according to claim 1, wherein the species are chosen from the Group IV elements.

9. (Once Amended) A method according to claim 1, wherein the substrate comprises a semiconductor such as Gallium-Arsenide.

10. (Once Amended) A method according to claim 1, wherein one of the precursors is heated to its decomposition temperature by heating the substrate.

12. (Once Amended) A method according to claim 10, wherein the substrate is heated to a temperature in the range 550-800°C.

13. (Once Amended) A method according to claim 1, wherein one of the precursors is heated to its decomposition temperature at a location adjacent the region.

15. (Once Amended) A method according to claim 1, further comprising moving the region across the substrate.

19. (Once Amended) Apparatus according to claim 18, wherein the second heating means is provided in or adjacent the slot.

20. (Once Amended) Apparatus according to claim 16, wherein the second heating means is in the form of a heating wire.

21. (Once Amended) Apparatus according to claim 16, wherein the first heating means is located at a position to heat the substrate support.

22. (Once Amended) Apparatus according to claim 16, further comprising means for causing relative movement between the substrate support and at least one of the inlets.

23. (Once Amended) Apparatus according to claim 17, further comprising means for causing relative movement between the substrate support and at least one of the inlets, wherein a plurality of supply conduits are provided for supplying the same or different precursors to regions on the substrate, the conduits and substrate

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